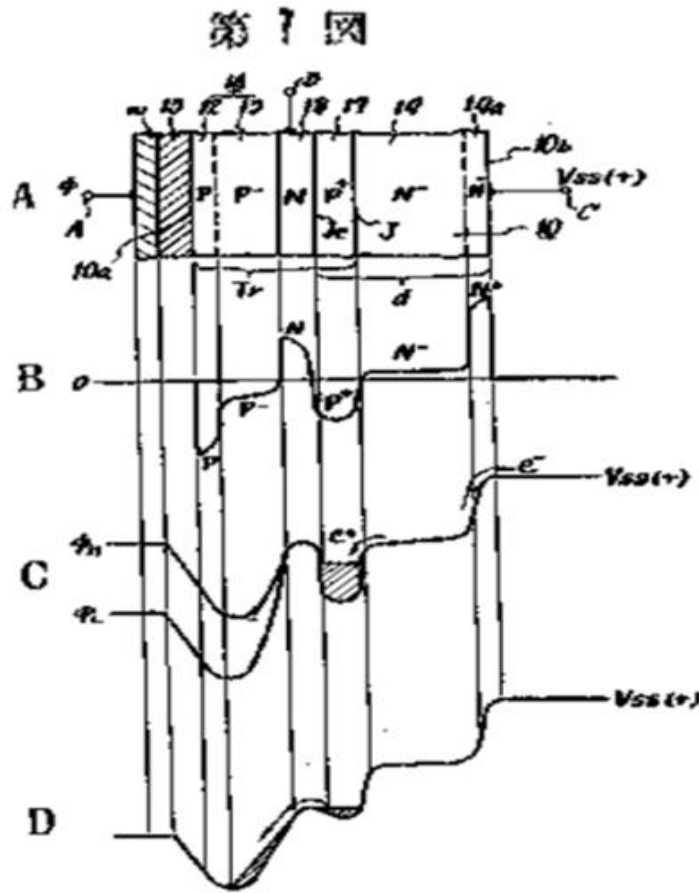


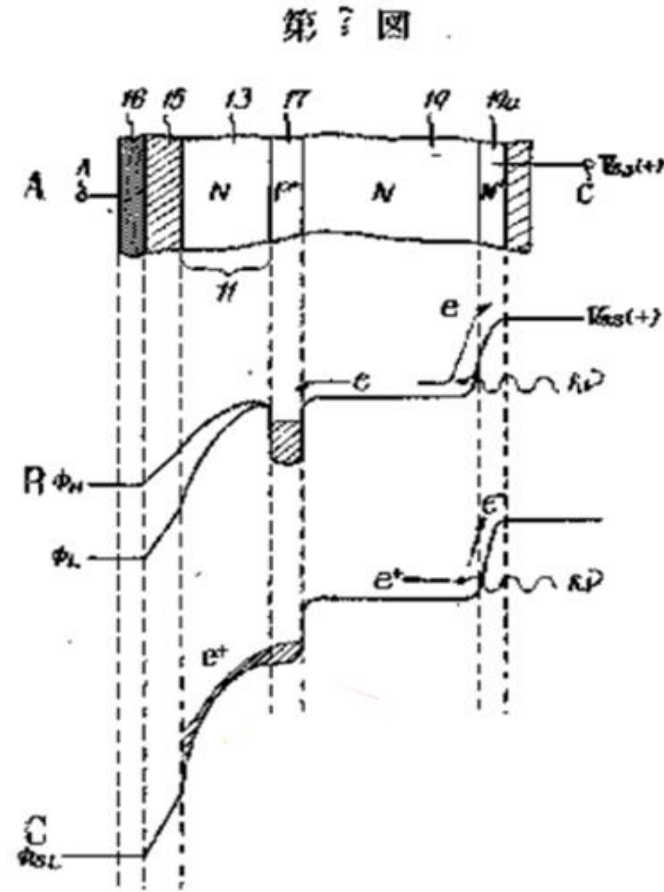
(1) Fig.7 of JPA1975-127646

N+NP+NP-P junction Pinned Photodiode with Global Shutter and Electric Shutter Capability with no Image Lag.



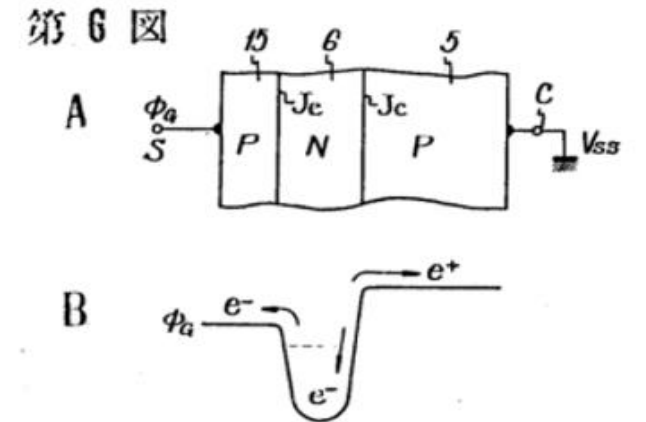
(2) Fig.7 of JPA1975-127647

N+NP+N junction Pinned Photodiode with Global Shutter and Electric Shutter Capability with No Image Lag.



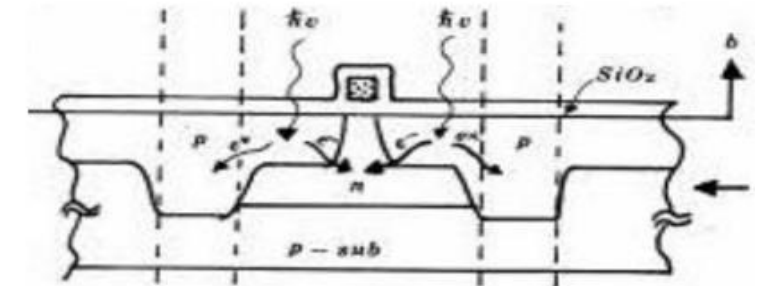
(3) Fig.6 of JPA1975-134985

PNP junction Pinned Photodiode with Vertical Overflow Drain (VOD) and Empty Potential Well of Complete Charge Transfer and No Image Lag



(4) Fig.6 of SSDM1978 Sony Paper

PNP junction Pinned Buried Photodiode with the heavily doped channel stops



Pinned Buried Photodiode with Vertical Overflow Drain (VOD) and Electric Shutter Function invented by Hagiwara at Sony in 1975 and developed by Hagiwara Team at Sony in 1978.